

V. S. Nageswara Rao Sunkaranam

List of Publications by Year in descending order

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76
papers

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726
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Dopant segregation and giant magnetoresistance in manganese-doped germanium. <i>Physical Review B</i> , 2007, 75, . | 3.2 | 88 |
| 2 | Femtosecond Ablation of Silicon in Acetone: Tunable Photoluminescence from Generated Nanoparticles and Fabrication of Surface Nanostructures. <i>Journal of Physical Chemistry C</i> , 2014, 118, 7139-7151. | 3.1 | 53 |
| 3 | Femtosecond Laser-Induced, Nanoparticle-Embedded Periodic Surface Structures on Crystalline Silicon for Reproducible and Multi-utility SERS Platforms. <i>ACS Omega</i> , 2018, 3, 18420-18432. | 3.5 | 46 |
| 4 | Synthesis of ultra-small silicon nanoparticles by femtosecond laser ablation of porous silicon. <i>Journal of Materials Science</i> , 2015, 50, 1666-1672. | 3.7 | 31 |
| 5 | Three-dimensional hybrid silicon nanostructures for surface enhanced Raman spectroscopy based molecular detection. <i>Journal of Applied Physics</i> , 2018, 123, . | 2.5 | 31 |
| 6 | Vibrational Lifetimes and Frequency-Gap Law of Hydrogen Bending Modes in Semiconductors. <i>Physical Review Letters</i> , 2006, 96, 035501. | 7.8 | 30 |
| 7 | SHI induced effects on the electrical and optical properties of HfO ₂ thin films deposited by RF sputtering. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2016, 379, 230-234. | 1.4 | 25 |
| 8 | Electronic excitation induced defect dynamics in HfO ₂ based MOS devices investigated by <i>in-situ</i> electrical measurements. <i>Applied Physics Letters</i> , 2018, 112, . | 3.3 | 25 |
| 9 | Synthesis of CuO hollow nanoparticles using laser ablation: effect of fluence and solvents. <i>Applied Physics A: Materials Science and Processing</i> , 2020, 126, 1. | 2.3 | 25 |
| 10 | Synthesis, characterization and radiation damage studies of high-k dielectric (HfO ₂) films for MOS device applications. <i>Radiation Effects and Defects in Solids</i> , 2015, 170, 207-217. | 1.2 | 22 |
| 11 | Ion induced crystallization and grain growth of hafnium oxide nano-particles in thin-films deposited by radio frequency magnetron sputtering. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 505301. | 2.8 | 21 |
| 12 | Gamma irradiation-induced effects on the electrical properties of HfO ₂ -based MOS devices. <i>Radiation Effects and Defects in Solids</i> , 2016, 171, 77-86. | 1.2 | 20 |
| 13 | Multi-functional gallium arsenide nanoparticles and nanostructures fabricated using picosecond laser ablation. <i>Applied Surface Science</i> , 2022, 589, 152802. | 6.1 | 20 |
| 14 | Silicon Nanostructures for Molecular Sensing: A Review. <i>ACS Applied Nano Materials</i> , 2022, 5, 4550-4582. | 5.0 | 20 |
| 15 | Structural and optical properties of porous silicon prepared by anodic etching of irradiated silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2013, 315, 188-191. | 1.4 | 18 |
| 16 | Grain fragmentation and phase transformations in hafnium oxide induced by swift heavy ion irradiation. <i>Applied Physics A: Materials Science and Processing</i> , 2018, 124, 1. | 2.3 | 17 |
| 17 | Trace level detection of explosives and pesticides using robust, low-cost, free-standing silver nanoparticles decorated porous silicon. <i>Optics Express</i> , 2021, 29, 30045. | 3.4 | 17 |
| 18 | dE/dx measurements for heavy ions with Z=6 in polycarbonate. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2002, 194, 7-14. | 1.4 | 16 |

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|----|--|-----|-----------|
| 19 | Studies on linear, nonlinear optical and excited state dynamics of silicon nanoparticles prepared by picosecond laser ablation. AIP Advances, 2015, 5, . | 1.3 | 16 |
| 20 | Robust and cost-effective silver dendritic nanostructures for SERS-based trace detection of RDX and ammonium nitrate. RSC Advances, 2020, 10, 44747-44755. | 3.6 | 16 |
| 21 | Studies of electronic sputtering of fullerene under swift heavy ion impact. Nuclear Instruments & Methods in Physics Research B, 2002, 190, 169-172. | 1.4 | 15 |
| 22 | Ion beam studies of Hafnium based alternate high-k dielectric films deposited on silicon. Nuclear Instruments & Methods in Physics Research B, 2014, 332, 389-392. | 1.4 | 14 |
| 23 | Ion induced intermixing and consequent effects on the leakage currents in HfO ₂ /SiO ₂ /Si systems. Applied Physics A: Materials Science and Processing, 2017, 123, 1. | 2.3 | 14 |
| 24 | Solvents Effect on the Morphology and Stability of Cu/CuO Nanoparticles Synthesized at High Fluence Laser Ablation. ChemistrySelect, 2019, 4, 10471-10482. | 1.5 | 14 |
| 25 | Radiation tolerance, charge trapping, and defect dynamics studies of ALD-grown Al/HfO ₂ /Si nMOSCAPs. Journal of Materials Science: Materials in Electronics, 2020, 31, 3312-3322. | 2.2 | 14 |
| 26 | Hafnium oxide nanoparticles fabricated by femtosecond laser ablation in water. Applied Physics A: Materials Science and Processing, 2019, 125, 1. | 2.3 | 13 |
| 27 | Development of a large area two-dimensional position sensitive $\hat{\mu}$ E $\hat{\alpha}$ E detector telescope for material analysis. Nuclear Instruments & Methods in Physics Research B, 2003, 212, 545-550. | 1.4 | 11 |
| 28 | Depth dependent modification of optical constants arising from H ⁺ implantation in n-type 4H-SiC measured using coherent acoustic phonons. APL Photonics, 2016, 1, . | 5.7 | 11 |
| 29 | Influence of the bottom metal electrode and gamma irradiation effects on the performance of HfO ₂ -based RRAM devices. Radiation Effects and Defects in Solids, 2019, 174, 66-75. | 1.2 | 11 |
| 30 | Fabrication of porous silicon based tunable distributed Bragg reflectors by anodic etching of irradiated silicon. Nuclear Instruments & Methods in Physics Research B, 2015, 358, 105-111. | 1.4 | 10 |
| 31 | Ion beam studies in strained layer superlattices. Nuclear Instruments & Methods in Physics Research B, 2002, 193, 319-323. | 1.4 | 9 |
| 32 | Ion beam characterization and engineering of strain in semiconductor multi-layers. Nuclear Instruments & Methods in Physics Research B, 2003, 212, 442-450. | 1.4 | 9 |
| 33 | Effects of swift heavy ion irradiation on the performance of HfO ₂ -based resistive random access memory devices. Journal of Materials Science: Materials in Electronics, 2021, 32, 2973-2986. | 2.2 | 9 |
| 34 | Effect of energetic ions on the stability of bond-center hydrogen in silicon. Physical Review B, 2007, 75, . | 3.2 | 8 |
| 35 | 150MeV Au ion induced modification of Si nanoparticles prepared by laser ablation. Nuclear Instruments & Methods in Physics Research B, 2014, 333, 99-105. | 1.4 | 8 |
| 36 | Effects of ion irradiation on the structural and electrical properties of HfO ₂ /SiON/Si p-metal oxide semiconductor capacitors. Thin Solid Films, 2019, 682, 156-162. | 1.8 | 8 |

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|----|---|-----|-----------|
| 37 | Structural investigations of picosecond laser ablated GaAs nanoparticles in different liquids. Nano Structures Nano Objects, 2020, 23, 100509. | 3.5 | 8 |
| 38 | Hafnia-based resistive switching devices for non-volatile memory applications and effects of gamma irradiation on device performance. Radiation Effects and Defects in Solids, 2018, 173, 239-249. | 1.2 | 7 |
| 39 | Blue luminescent silicon nanoparticles synthesized from free-standing porous silicon layer by ultrasonic treatment. Optical Materials, 2015, 48, 66-70. | 3.6 | 6 |
| 40 | Effect of growth rate on crystallization of HfO ₂ thin films deposited by RF magnetron sputtering. AIP Conference Proceedings, 2016, , . | 0.4 | 6 |
| 41 | Swift heavy ion assisted growth of silver nanoparticles embedded in hafnium oxide matrix. Journal of Applied Physics, 2021, 130, . | 2.5 | 6 |
| 42 | Ion channeling, high resolution x-ray diffraction and Raman spectroscopy in strained quantum wells. Journal of Applied Physics, 2001, 90, 2824-2830. | 2.5 | 5 |
| 43 | One dimensional silicon nanostructures prepared by oxidized porous silicon under heat treatment. Applied Surface Science, 2014, 320, 334-338. | 6.1 | 5 |
| 44 | Fabrication of HfO ₂ based MOS and RRAM devices: A study of thermal annealing effects on these devices. AIP Conference Proceedings, 2019, , . | 0.4 | 5 |
| 45 | Laser annealing of Au/HfO ₂ bi-layers to fabricate Au nanoparticles without altering the phase of HfO ₂ for applications in SERS and memory devices. Journal of Materials Science: Materials in Electronics, 2022, 33, 6657-6669. | 2.2 | 5 |
| 46 | Resistivity dependence on nanostructure formation in picosecond ablation of silicon and SERS-based sensing applications. Journal Physics D: Applied Physics, 2022, 55, 405103. | 2.8 | 5 |
| 47 | Quantum description for the effects of strained layered superlattices on channeling radiation. Nuclear Instruments & Methods in Physics Research B, 2003, 202, 312-316. | 1.4 | 4 |
| 48 | Energy dependence relations for positron channeling critical angle and dechanneling probability due to stacking faults. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 2312-2317. | 1.4 | 4 |
| 49 | Ion beam-mixing effects in nearly lattice-matched AlInN/GaN heterostructures by swift heavy ion irradiation. Radiation Effects and Defects in Solids, 2012, 167, 506-511. | 1.2 | 4 |
| 50 | Synthesis and tailoring of GaN nanocrystals at room temperature by RF magnetron sputtering. Radiation Effects and Defects in Solids, 2012, 167, 659-665. | 1.2 | 4 |
| 51 | Effects of growth parameters on HfO ₂ thin-films deposited by RF Magnetron sputtering. Radiation Effects and Defects in Solids, 2022, 177, 15-26. | 1.2 | 4 |
| 52 | Ion beam induced modification of lattice strains in In _{0.1} Ga _{0.9} As/GaAs system. Nuclear Instruments & Methods in Physics Research B, 2003, 212, 473-476. | 1.4 | 3 |
| 53 | Fabrication and characterization of GaAs nanoparticles achieved using femtosecond laser ablation. Materials Today: Proceedings, 2020, 33, 2385-2389. | 1.8 | 3 |
| 54 | Strain measurements of semiconductor multilayers by ion channeling, high resolution XRD and Raman spectroscopy. AIP Conference Proceedings, 2001, , . | 0.4 | 2 |

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|----|--|-----|-----------|
| 55 | Channeling radiation from relativistic electrons – Study of stacking faults and dislocations. Nuclear Instruments & Methods in Physics Research B, 2002, 193, 188-191. | 1.4 | 2 |
| 56 | Study of Ag ion irradiation effects on the oxygen stoichiometry of La-2125-type superconducting thin films using ERDA. Radiation Measurements, 2003, 36, 733-736. | 1.4 | 2 |
| 57 | Ion Beam Studies Of Semiconductor Nanoparticles For The Integration Of Optoelectronic Devices. , 2011, , . | | 2 |
| 58 | Energetic ion induced desorption of hydrogen from porous silicon studied by on-line elastic recoil detection analysis. Microporous and Mesoporous Materials, 2017, 246, 81-88. | 4.4 | 2 |
| 59 | Metal nanoparticles in dielectric media: Physical vapor deposited HfO ₂ & Ag multilayers for MOS device and SPR applications. AIP Conference Proceedings, 2020, , . | 0.4 | 2 |
| 60 | Effects of Initial Grain Size and Laser Parameters on HfO ₂ Nanoparticles Prepared Using Femtosecond Laser Ablation in Liquids. Journal of Electronic Materials, 2021, 50, 1742-1751. | 2.2 | 2 |
| 61 | ION IRRADIATION EFFECTS AND ION BEAM STUDIES OF SEMICONDUCTOR MULTILAYERS. , 2003, , . | | 2 |
| 62 | 200 MeV Ag ion irradiation mediated green synthesis and self assembly of silver nanoparticles into dendrites for enhanced SERS applications. Radiation Physics and Chemistry, 2022, 193, 109966. | 2.8 | 2 |
| 63 | Automation of Channeling Experiment for Lattice Strain Measurements Using High Energy Ion Beams. AIP Conference Proceedings, 2003, , . | 0.4 | 1 |
| 64 | Ion Beam Studies of Strains/Defects in Semiconductor Multilayers. AIP Conference Proceedings, 2003, , . | 0.4 | 1 |
| 65 | Reconfiguration and dissociation of bonded hydrogen in silicon by energetic ions. Physical Review B, 2011, 83, . | 3.2 | 1 |
| 66 | 120 MeV Ag ion induced effects in Au/HfO ₂ /Si MOSCAPs. AIP Conference Proceedings, 2018, , . | 0.4 | 1 |
| 67 | Medium Energy Carbon and Nitrogen Ion Beam Induced Modifications in Charge Transport, Structural and Optical Properties of Ni/Pd/n-GaN Schottky Barrier Diodes. Materials, 2020, 13, 1299. | 2.9 | 1 |
| 68 | Ion Beams for synthesis and modification of nanostructures in semiconductors. Materials Research Society Symposia Proceedings, 2011, 1354, 79. | 0.1 | 0 |
| 69 | RBS, XRD, Raman and AFM Studies of Microwave Synthesized Ge Nanocrystals. Materials Research Society Symposia Proceedings, 2011, 1354, 141. | 0.1 | 0 |
| 70 | Structural Changes Induced by Swift Heavy Ion Beams in tensile strained Al (1-x)In _x N /GaN Hetero-structures. Materials Research Society Symposia Proceedings, 2011, 1354, 115. | 0.1 | 0 |
| 71 | Anharmonic effects on positron channeling angular scans and dechanneling due to stacking faults and platelets. Radiation Effects and Defects in Solids, 2012, 167, 594-606. | 1.2 | 0 |
| 72 | Ion induced effects on the dissociation of silicon nanoparticles. AIP Conference Proceedings, 2017, , . | 0.4 | 0 |

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|----|---|-----|-----------|
| 73 | Formation and local heating effects on the vibrational properties of H ₂ * defects in crystalline silicon. AIP Conference Proceedings, 2018, , . | 0.4 | 0 |
| 74 | Effects of thermal annealing and gamma irradiation on HfO ₂ thin films deposited on GaAs. AIP Conference Proceedings, 2019, , . | 0.4 | 0 |
| 75 | Ar Ion Irradiation Effects on the Characteristics of Ru Pt n-GaN Schottky Barrier Diodes. Semiconductors, 2020, 54, 1641-1649. | 0.5 | 0 |
| 76 | 120â€‰MeV Ag ion irradiation induced intermixing, grain fragmentation in HfO ₂ /GaO _x thin films and consequent effects on the electrical properties of HfO ₂ /GaO _x /Si-based MOS capacitors. Radiation Effects and Defects in Solids, 2020, 175, 150-159. | 1.2 | 0 |